



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

1N5817-1N5819

DO-41 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High Surge current capability 高浪涌电流能力
Case 封装:DO-41



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	1N5817	1N5818	1N5819	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	V
Forward Rectified Current 正向整流电流	I_F	1			A
Peak Surge Current 峰值浪涌电流	I_{FSM}	25			A
Repetitive Peak Surge Current 重复峰值浪涌电流	I_{FRM}	2			A
Power Dissipation 耗散功率	P_D	1500			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	80			$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	-50to+150 $^{\circ}\text{C}$			$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817W	B5818W	B5819W	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	20	30	40	V	$I_R=1\text{mA}$
Forward Voltage 正向电压	V_F	0.45	0.55	0.6	V	$I_F=1\text{A}$
Reverse Current 反向电流	I_R	1			mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_T	120			pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

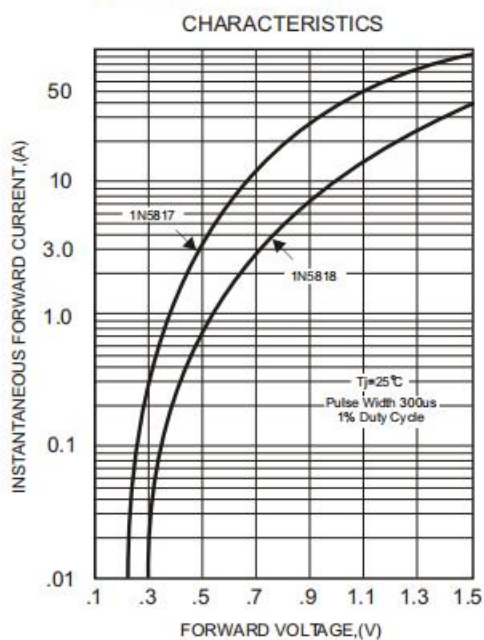


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

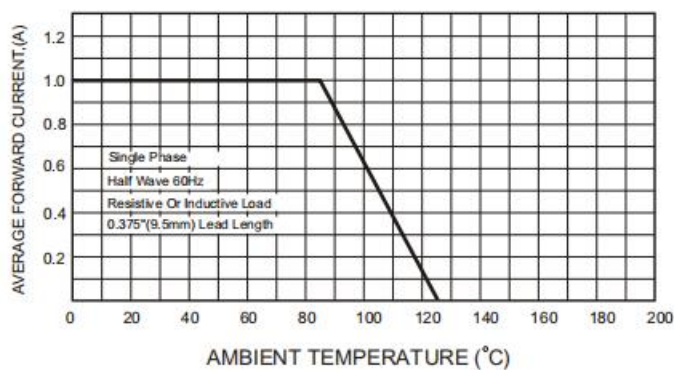


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

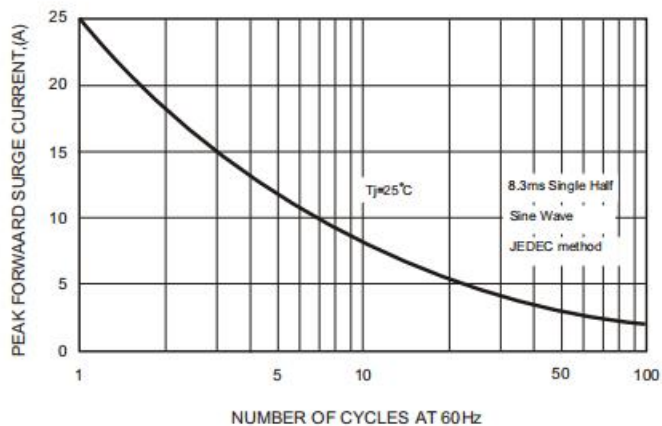


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

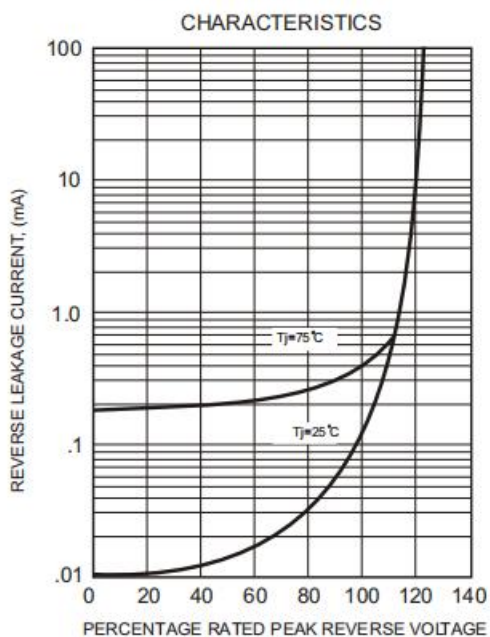
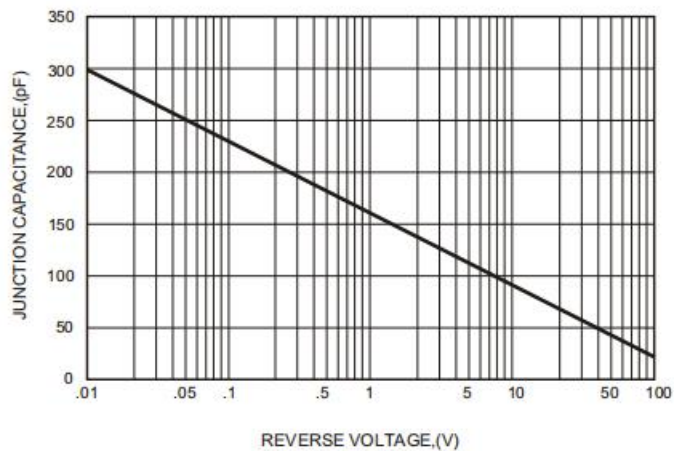


FIG.5-TYPICAL JUNCTION CAPACITANCE



■ Dimension 外形封装尺寸

